

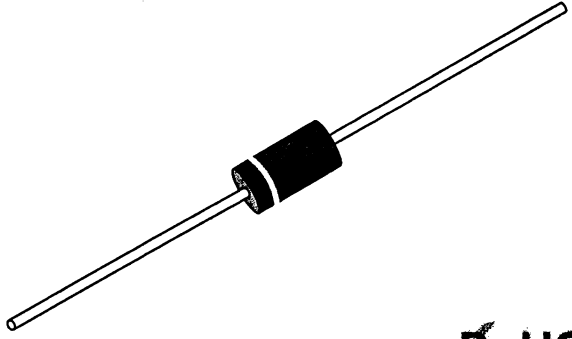
*New Jersey Semi-Conductor Products, Inc.*

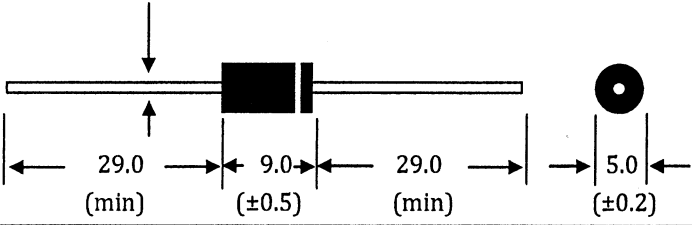
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**1N6527**

**0.25A 10kV 70nS**

<b>Introduce:</b>	<b>Reference Shape:</b>
High voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.	
<b>Features:</b>	
High reliability design. GPP chip. High frequency, super fast recovery. Conform to RoHS and SGS. Epoxy resin molded in vacuumHave anticorrosion in the surface.	

<b>Applications:</b>		<b>Unit: (mm)</b>
High voltage multiplier circuit. X-ray power supply. General purpose high voltage rectifier. Other:	DO-590 Lead Diameter 1.28±0.03 	
<b>Mechanical Data:</b>		
Case: epoxy resin molding. Terminal: welding axis. Net weight: 2.1 grams (approx).		

**Maximum Ratings And Characteristics: (Absolute Maximum Ratings)**

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	T <sub>A</sub> =25°C	10	kV
Non-Repetitive Peak Reverse Voltage	V <sub>RSM</sub>	T <sub>A</sub> =25°C	--	kV
Average Forward Current Maximum	I <sub>FAVM</sub>	T <sub>A</sub> =55°C	0.25	A
		T <sub>L</sub> =100°C (L=0.375")	0.13	A
Non-Repetitive Forward Surge Current	I <sub>FSM</sub>	T <sub>A</sub> =25°C; 60Hz Half-Sine Wave; 8.3mS	15	A
Junction Temperature	T <sub>J</sub>		150	°C
Allowable Operation Case Temperature	T <sub>C</sub>		-55~+150	°C
Storage Temperature	T <sub>STG</sub>		-55~+175	°C

**Electrical Characteristics: T<sub>A</sub>=25°C (Unless Otherwise Specified)**

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V <sub>FM</sub>	at 25°C; at I <sub>FAVM</sub>	12	V
Maximum Reverse Current	I <sub>R1</sub>	at 25°C; at V <sub>RRM</sub>	0.5	uA
	I <sub>R2</sub>	at 100°C; at V <sub>RRM</sub>	20	uA
Maximum Reverse Recovery Time	T <sub>RR</sub>	at 25°C; I <sub>F</sub> =0.5I <sub>R</sub> ; I <sub>R</sub> =I <sub>FAVM</sub> ; I <sub>RR</sub> =0.25I <sub>R</sub>	70	nS
Junction Capacitance	C <sub>J</sub>	at 25°C; V <sub>R</sub> =50VDC; f=1KHz	2.5	pF

